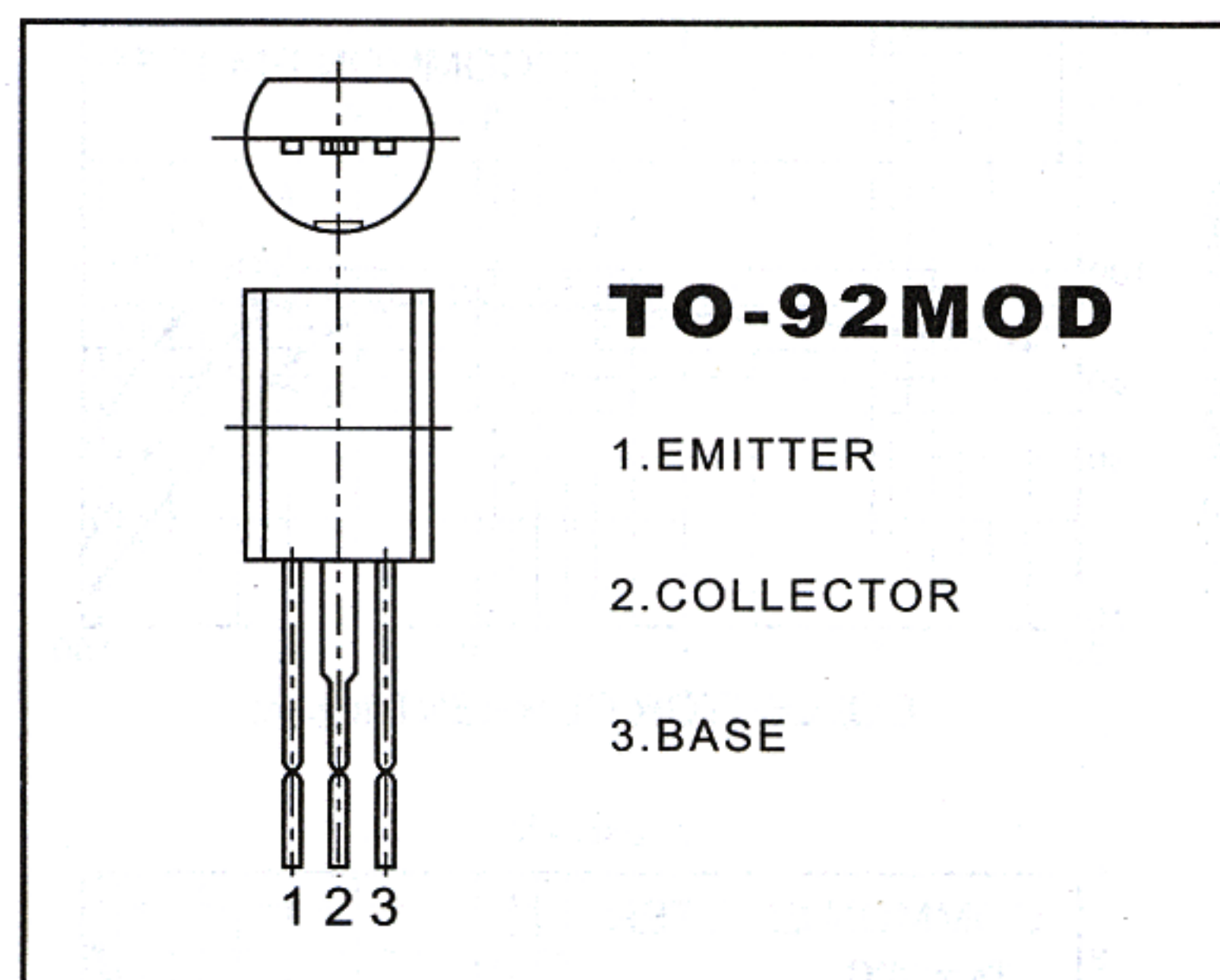


2SC2482 TRANSISTOR(NPN)



FEATURES

Power dissipation

P_{CM} : 0.9W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : 0.1 A

Collector-base voltage

$V_{(BR)CBO}$: 300 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

ELECTRICAL CHARACTERISTICS

($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 100 \mu A, I_E = 0$	300		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 3 mA, I_B = 0$	300		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 100 \mu A, I_C = 0$	7		V
Collector cut-off current	I_{CBO}	$V_{CB} = 240 V, I_E = 0$		1	μA
Collector cut-off current	I_{CEO}	$V_{CE} = 220 V, I_B = 0$		5	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 7 V, I_C = 0$		1	μA
DC current gain	h_{FE}	$V_{CE} = 10 V, I_C = 20 mA$	30	150	
Collector-emitter saturation voltage	V_{CEsat}	$I_C = 10 mA, I_B = 1 mA$		1	V
Base-emitter saturation voltage	V_{BEsat}	$I_C = 10 mA, I_B = 1 mA$		1	V
Transition frequency	f_T	$V_{CE} = 10 V, I_C = 20 mA$ $f = 30 MHz$	50		MHz

CLASSIFICATION OF h_{FE}

Rank	O	Y
Range	30-90	90-150

Typical Characteristics

2SC2482

